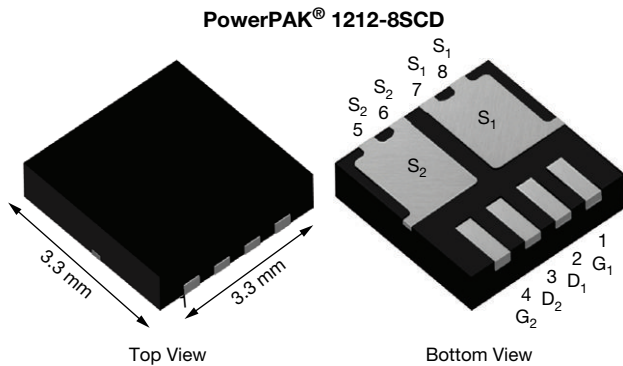




**THE DATASHEET OF  
SISF00DN-T1-GE3**



# Common Drain Dual N-Channel 30 V (S1-S2) MOSFET



PRODUCT SUMMARY	
$V_{S1S2}$ (V)	30
$R_{S1S2(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.005
$R_{S1S2(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.007
$Q_g$ typ. (nC)	16.1 <sup>h</sup>
$I_{S1S2}$ (A)	60 <sup>a, g</sup>
Configuration	Common drain

## FEATURES

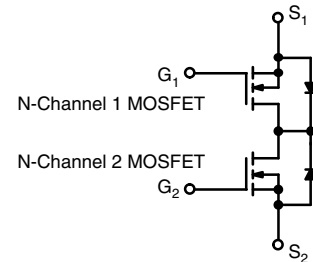
- TrenchFET® Gen IV power MOSFET
- Very low source-to-source on resistance
- Integrated common-drain n-channel MOSFETs in a compact and thermally enhanced package
- 100 %  $R_g$  and UIS tested
- Optimizes circuit layout for bi-directional current flow
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Battery management
- Load switching



ORDERING INFORMATION	
Package	PowerPAK 1212-8SCD
Lead (Pb)-free and halogen-free	SiSF00DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	$V_{S1S2}$	30	V	
Gate-source voltage	$V_{GS}$	+20 / -16		
Continuous drain current ( $T_J = 150$ °C)	$I_{S1S2}$	$T_C = 25$ °C	60 <sup>a</sup>	A
		$T_C = 70$ °C	60 <sup>a</sup>	
		$T_A = 25$ °C	25.5 <sup>b, c</sup>	
		$T_A = 70$ °C	20.4 <sup>b, c</sup>	
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{S1S2M}$	120		
Maximum power dissipation	$P_D$	$T_C = 25$ °C	69.4	W
		$T_C = 70$ °C	44.4	
		$T_A = 25$ °C	5.2 <sup>b, c</sup>	
		$T_A = 70$ °C	3.3 <sup>b, c</sup>	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C	
Soldering recommendations (peak temperature) <sup>c</sup>		260		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient <sup>b</sup>	$R_{thJA}$	19	24	°C/W	
Maximum junction-to-case (drain)	$R_{thJC}$	1.4	1.8		

### Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8SCD is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 63 °C/W
- $T_C = 25$  °C
- Single MOSFET



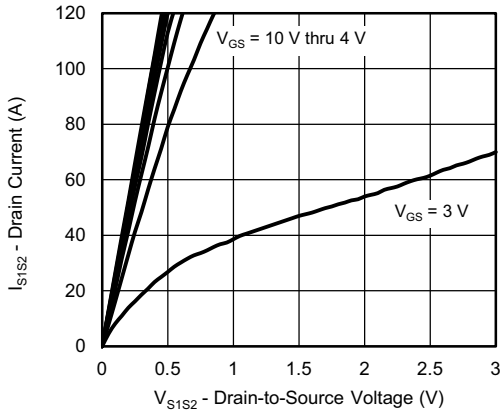
SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	30	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{S1S2} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	1	-	2.1	V
Gate-source leakage	$I_{GSS}$	$V_{S1S2} = 0\text{ V}$ , $V_{GS} = +20 / -16\text{ V}$	-	-	100	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{S1S2} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{S1S2} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 70\text{ }^\circ\text{C}$	-	-	15	
On-state drain current <sup>a</sup>	$I_{S1S2(on)}$	$V_{S1S2} \geq 10\text{ V}$ , $V_{GS} = 10\text{ V}$	20	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{S1S2(on)}$	$V_{GS} = 10\text{ V}$ , $I_{S1S2} = 10\text{ A}$	-	0.0042	0.0050	$\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_{S1S2} = 5\text{ A}$	-	0.0056	0.0070	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{S1S2} = 15\text{ V}$ , $I_{S1S2} = 20\text{ A}$	-	130	-	S
<b>Dynamic <sup>b, c</sup></b>						
Input capacitance	$C_{ISS}$	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	-	2700	-	$\mu\text{F}$
Output capacitance	$C_{OSS}$		-	865	-	
Reverse transfer capacitance	$C_{RSS}$		-	51	-	
Total gate charge	$Q_g$	$V_{DS} = 15\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 10\text{ A}$	-	35	53	nC
		$V_{DS} = 15\text{ V}$ , $V_{GS} = 4.5\text{ V}$ , $I_D = 10\text{ A}$	-	16.1	24.2	
Gate-source charge	$Q_{gs}$	$V_{DS} = 15\text{ V}$ , $V_{GS} = 4.5\text{ V}$ , $I_D = 10\text{ A}$	-	7	-	nC
Gate-drain charge	$Q_{gd}$		-	2.5	-	
Gate resistance	$R_g$	$f = 1\text{ MHz}$	0.3	1.5	3	$\Omega$
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$ , $R_L = 1\text{ }\Omega$ , $I_{S1S2} \cong 10\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\text{ }\Omega$	-	10	20	ns
Rise time	$t_r$		-	32	65	
Turn-off delay time	$t_{d(off)}$		-	22	45	
Fall time	$t_f$		-	10	20	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$ , $R_L = 1\text{ }\Omega$ , $I_D \cong 10\text{ A}$ , $V_{GEN} = 4.5\text{ V}$ , $R_g = 1\text{ }\Omega$	-	21	45	ns
Rise time	$t_r$		-	60	120	
Turn-off delay time	$t_{d(off)}$		-	25	50	
Fall time	$t_f$		-	15	30	
<b>Drain-Source Body Diode Characteristics <sup>c</sup></b>						
Continuous source-drain diode current	$I_{S1S2}$	$T_C = 25\text{ }^\circ\text{C}$	-	-	60	A
Pulse diode forward current	$I_{S1S2M}$		-	-	120	
Body diode reverse recovery time	$t_{rr}$	$I_F = 10\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $T_J = 25\text{ }^\circ\text{C}$	-	42	85	ns
Body diode reverse recovery charge	$Q_{rr}$		-	42	85	nC
Reverse recovery fall time	$t_a$		-	23	-	ns
Reverse recovery rise time	$t_b$		-	19	-	

**Notes**

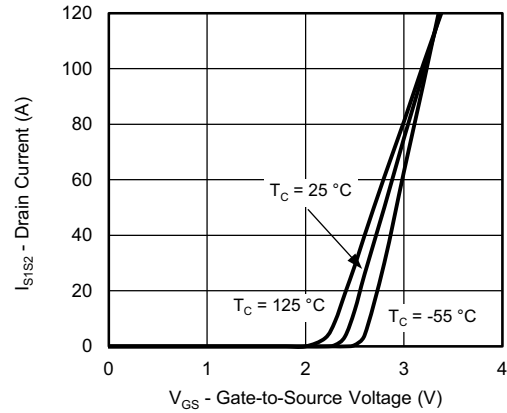
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- Guaranteed by design, not subject to production testing
- On single MOSFET

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

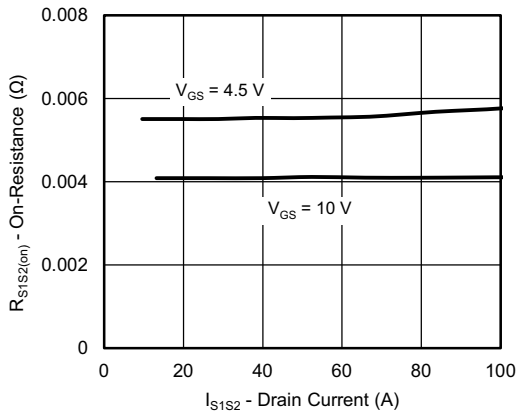
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



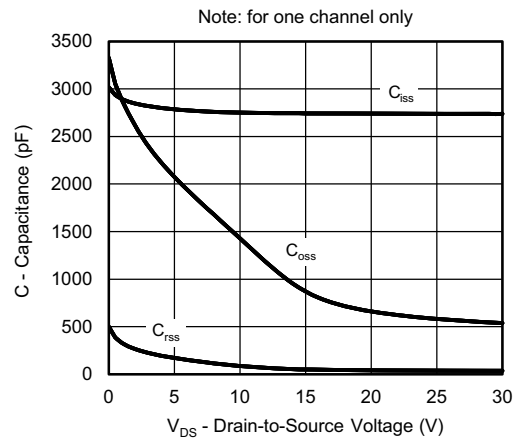
**Output Characteristics**



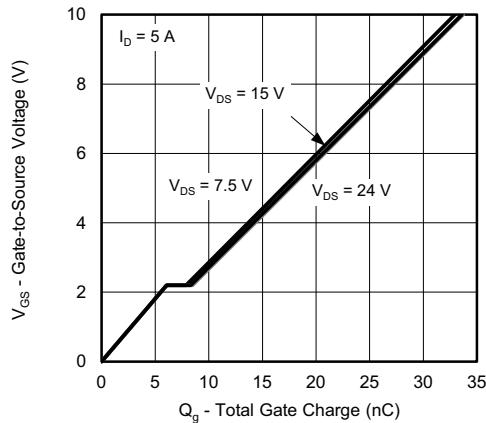
**Transfer Characteristics**



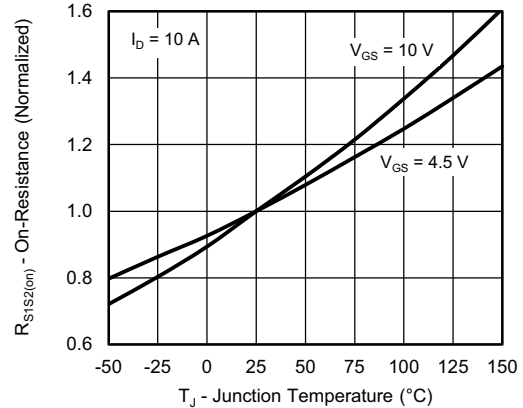
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

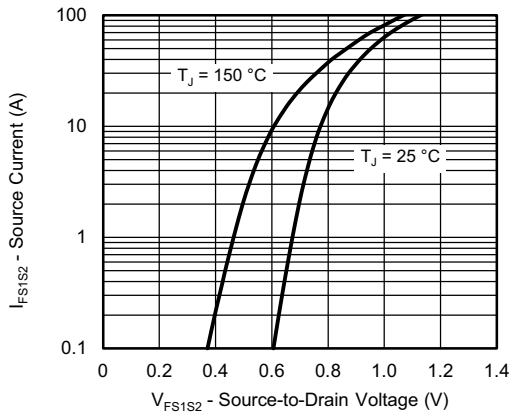


**Gate Charge**

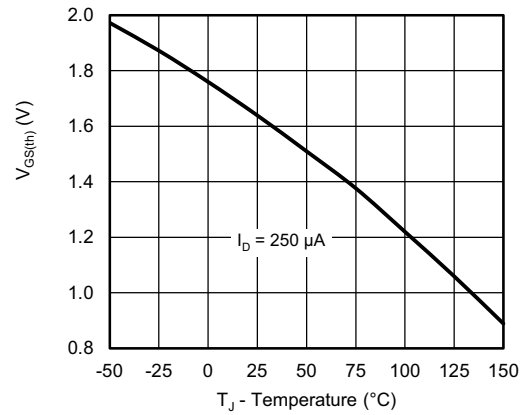


**On-Resistance vs. Junction Temperature**

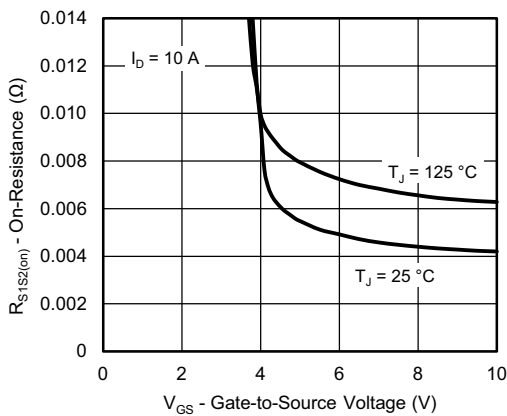
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



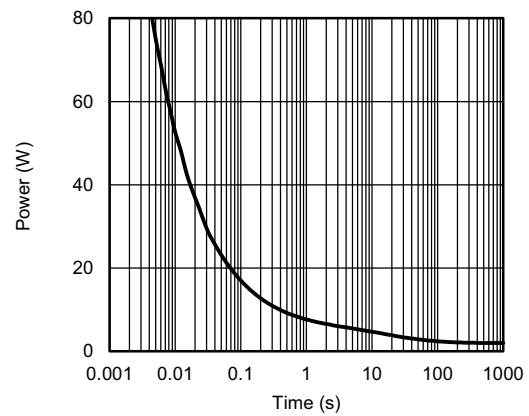
**Source-Drain Diode Forward Voltage**



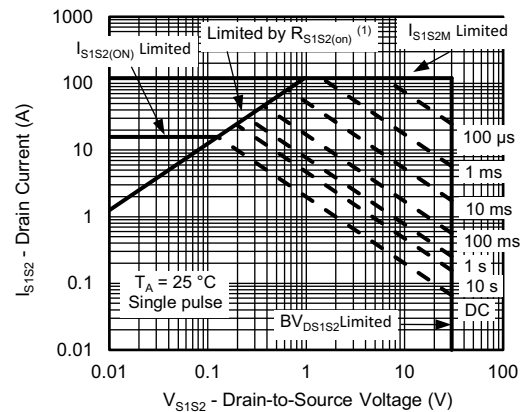
**Threshold Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



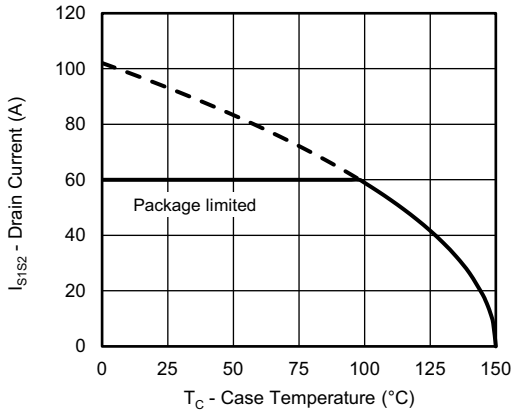
**Single Pulse Power, Junction-to-Ambient**



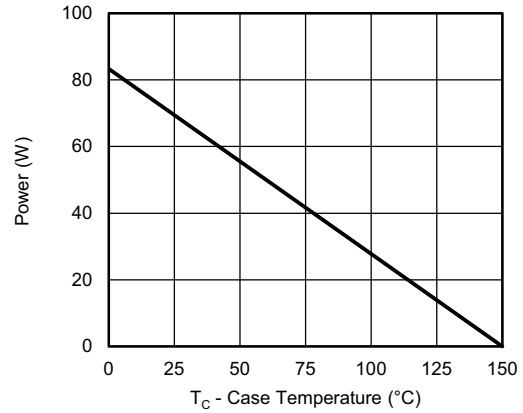
**Safe Operating Area, Junction-to-Ambient**



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



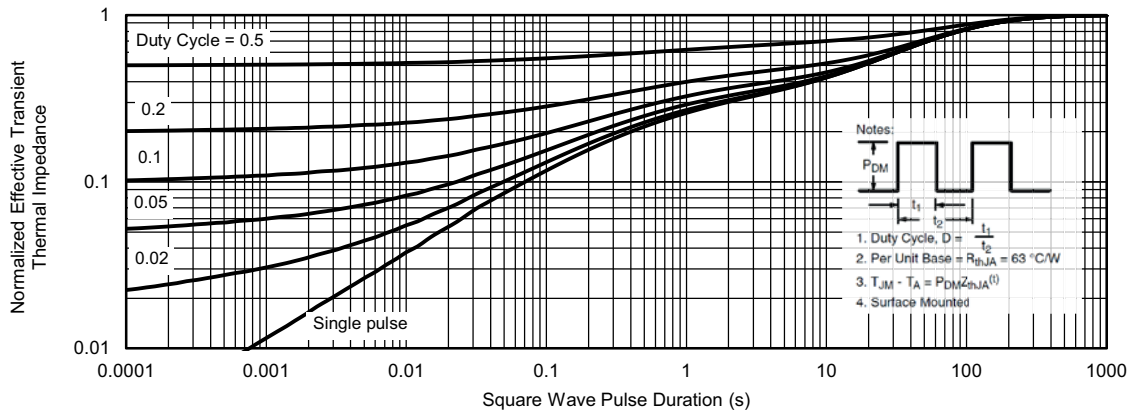
Current Derating <sup>a</sup>



Power, Junction-to-Case (Drain)

Note

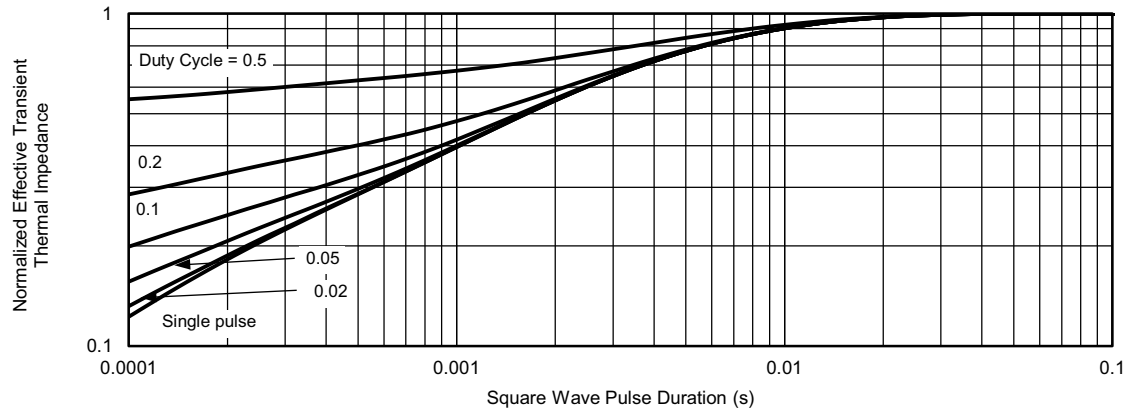
a. The power dissipation  $P_D$  is based on  $T_J \text{ max.} = 150 \text{ }^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



Normalized Thermal Transient Impedance, Junction-to-Ambient



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

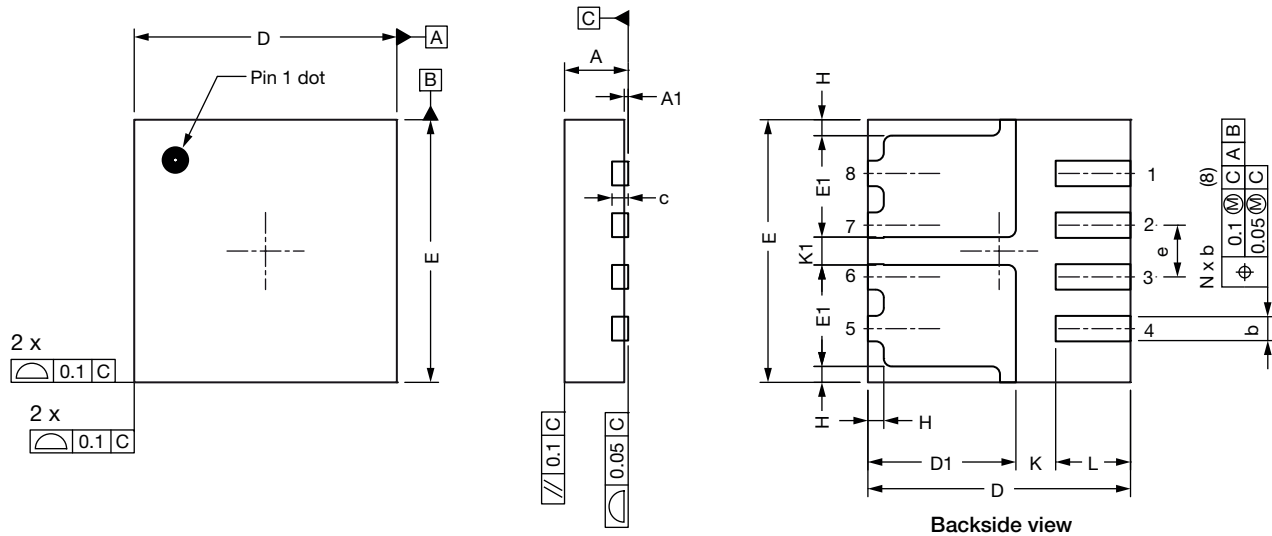


**Normalized Thermal Transient Impedance, Junction-to-Case (Drain)**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?75573](http://www.vishay.com/ppg?75573).



PowerPAK® 1212-8S CD with Flip Chip



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.027	0.029	0.031
A1	0	0.02	0.05	0	0.001	0.002
b	0.27	0.32	0.37	0.011	0.013	0.015
c	-	0.20 ref.	-	-	0.008 ref.	-
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	1.76	1.86	1.96	0.069	0.073	0.077
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	1.18	1.28	1.38	0.046	0.050	0.054
e	0.60	0.65	0.70	0.024	0.026	0.028
K	0.50 typ.			0.020 typ.		
K1	0.35 typ.			0.014 typ.		
H	0.10	0.20	0.30	0.006	0.008	0.010
L	0.84	0.94	1.04	0.033	0.037	0.041

ECN: C17-1732-Rev. A, 18-Dec-17  
DWG: 6061





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